

**IN THE SPECIFICATION:**

On page 5, first paragraph, please amend as follows:

A well 102 is formed on the substrate 100 having the element isolating film 104 according to an impurity implant process. Here, the element isolating film formation process may be performed after the well formation process, as depicted in Fig. 3B.

On page 5, second paragraph, please amend as follows:

Thereafter, a photolithography process and an impurity implant process are sequentially carried out in the memory cell array region I and the segment select region II of the substrate 100 having the well 102, thereby forming buried layers [[101]] 110, 111 aligned in one direction.

On page 10, first full paragraph, please amend as follows:

The flat cell type mask ROM includes: a substrate 200 where a memory cell array region and a segment select region are defined; first and second trenches 203, 205, as depicted in Fig. 8A, respectively formed at the outer portion of the memory cell array region and at the outer portion of a buried layer formation region of the segment select region; an ~~element isolating film 204~~ first isolation film 204 and an isolating pattern 206 respectively filling up the first and second trenches 203, 205; a plurality of buried layers 210 aligned on the substrate 200 in a first direction by a predetermined interval, and surrounded by the ~~isolating patter 206~~ second isolation film 206; and a plurality of gate insulating layers 212 and gates 214 aligned in a second direction to cross the buried layers 210 in an orthogonal direction.

On page 11, second paragraph, please amend as follows:

Thereafter, an insulating film such as an oxide silicon film is deposited over the resultant structure having the first and second trenches 203, 205, and etched according to an etch back process or a chemical mechanical polishing process, to form the ~~element isolating film 204~~ first isolation film 204 and the isolating pattern filling up the first and second trenches 203, 205.

On page 12, third full paragraph, please amend as follows:

Reference numeral 210 denote the buried layer formed in the memory cell array region III, and 211 denotes the buried layer formed in the ~~isolating pattern 206~~ second isolation film 206 of the segment select region IV.

On page 13, third full paragraph, please amend as follows:

Referring to Figure 8c, a protective film 220 is deposited on the substrate 200 and etched to form a contact 111 for exposing the buried layer 211 of the segment select region IV. The contact [[111]] 222 serves as a passage to a bit line to be formed according to a succeeding process.

Throughout, please replace “element isolating film 204” with “first isolation film 204.”

Throughout, please replace “isolating pattern 206” with “second isolation film 206.”

**IN THE DRAWINGS:**

Please cancel Figures 3A and 4 and substitute the enclosed marked up versions in red ink therefore.